Device Modeling Report

COMPONENTS: Power MOSFET (Model Parameters)
PART NUMBER: 2SJ683-TL-E
MANUFACTURER: SANYO
Body Diode (Model Parameters) / ESD Protection Diode

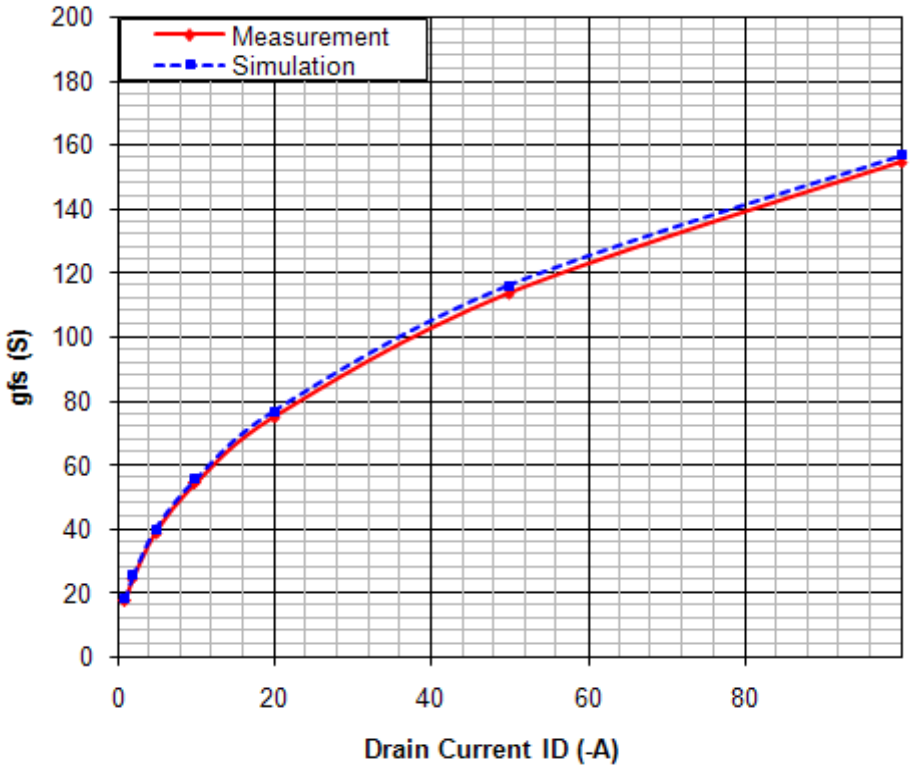
Bee Technologies Inc.

MOSFET MODEL

PSpice model parameter	Model description
LEVEL	
L	Channel Length
W	Channel Width
KP	Transconductance
RS	Source Ohmic Resistance
RD	Ohmic Drain Resistance
VTO	Zero-bias Threshold Voltage
RDS	Drain-Source Shunt Resistance
TOX	Gate Oxide Thickness
CGSO	Zero-bias Gate-Source Capacitance
CGDO	Zero-bias Gate-Drain Capacitance
CBD	Zero-bias Bulk-Drain Junction Capacitance
MJ	Bulk Junction Grading Coefficient
PB	Bulk Junction Potential
FC	Bulk Junction Forward-bias Capacitance Coefficient
RG	Gate Ohmic Resistance
IS	Bulk Junction Saturation Current
N	Bulk Junction Emission Coefficient
RB	Bulk Series Resistance
PHI	Surface Inversion Potential
GAMMA	Body-effect Parameter
DELTA	Width effect on Threshold Voltage
ETA	Static Feedback on Threshold Voltage
THETA	Mobility Modulation
KAPPA	Saturation Field Factor
VMAX	Maximum Drift Velocity of Carriers
XJ	Metallurgical Junction Depth
UO	Surface Mobility

Transconductance Characteristic

Circuit Simulation Result

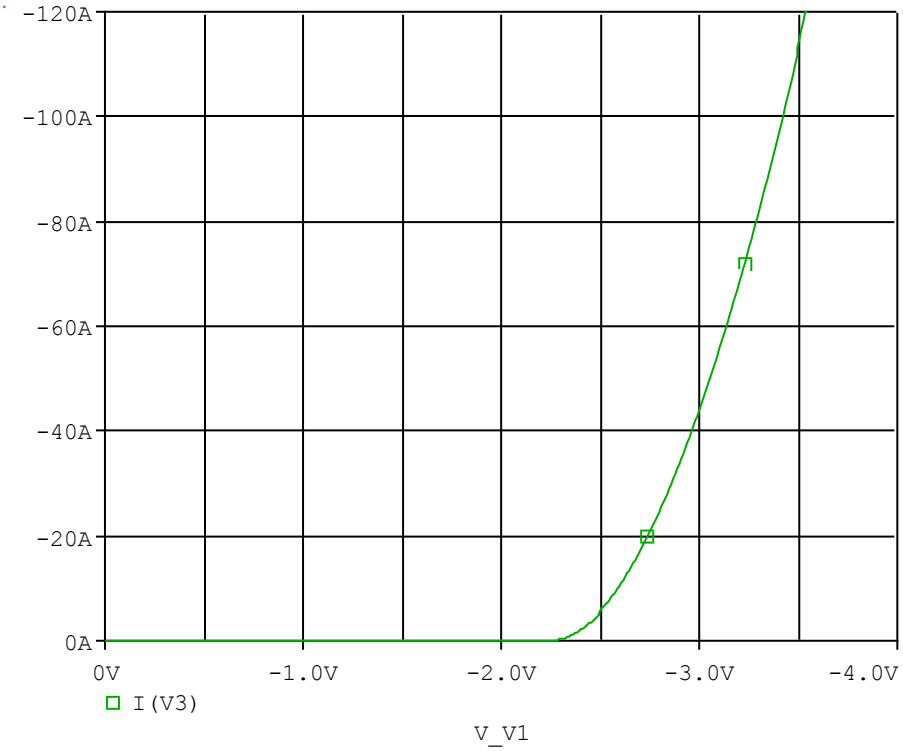


Comparison table

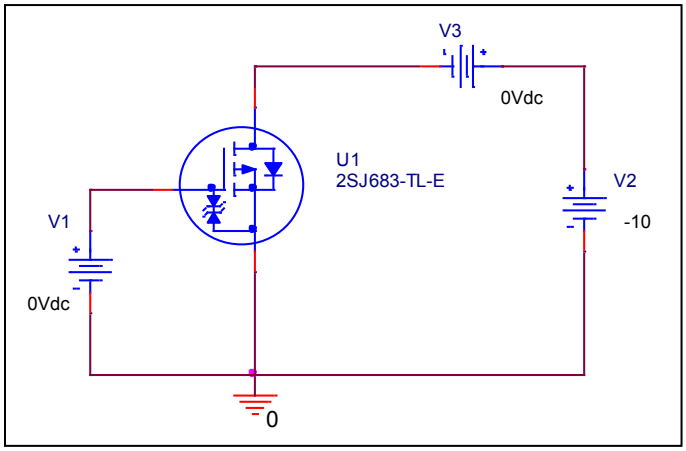
-Id(A)	gfs(S)		Error (%)
	Measurement	Simulation	
1	17.600	18.236	3.61
2	24.750	25.596	3.42
5	38.850	39.876	2.64
10	54.250	55.476	2.26
20	75.000	76.703	2.27
50	113.500	116.109	2.30
100	154.500	156.691	1.42

Vgs-Id Characteristic

Circuit Simulation result

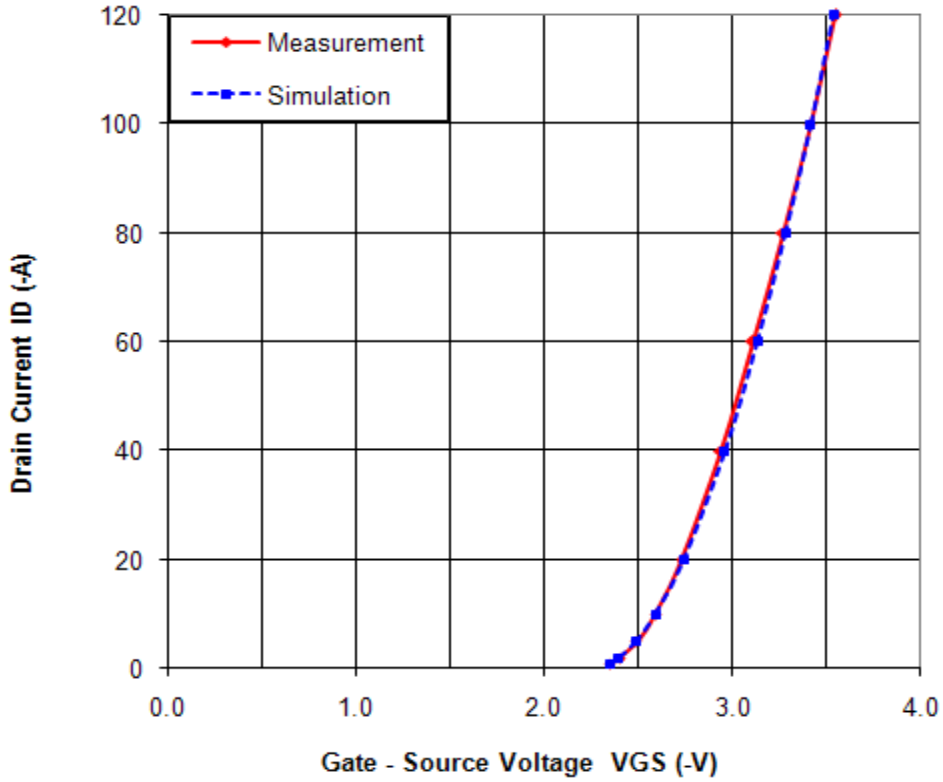


Evaluation circuit



Comparison Graph

Circuit Simulation Result

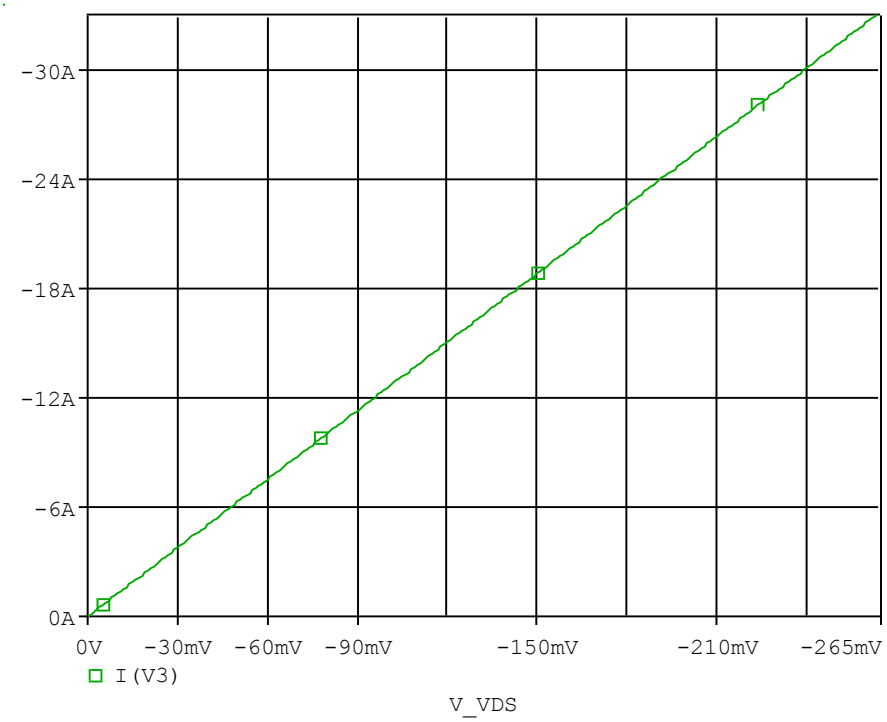


Simulation Result

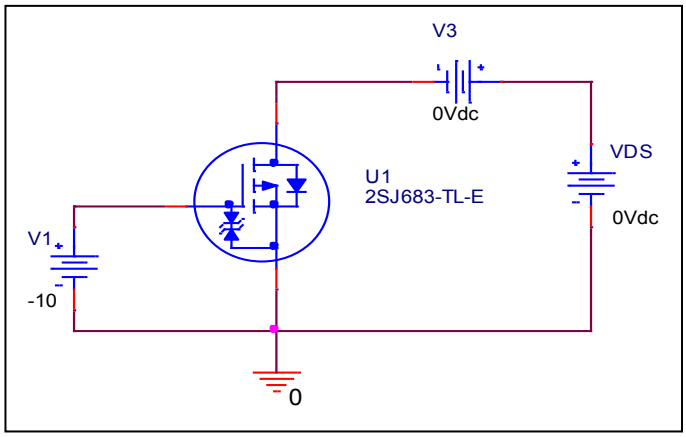
$-I_D$(mA)	$-V_{GS}$(V)		Error (%)
	Measurement	Simulation	
1	2.350	2.350	0.00
2	2.400	2.395	-0.21
5	2.490	2.487	-0.12
10	2.595	2.592	-0.12
20	2.730	2.742	0.44
40	2.940	2.962	0.75
60	3.110	3.135	0.80
80	3.270	3.284	0.43
100	3.415	3.418	0.09
120	3.550	3.541	-0.25

Rds(on) Characteristic

Circuit Simulation result



Evaluation circuit

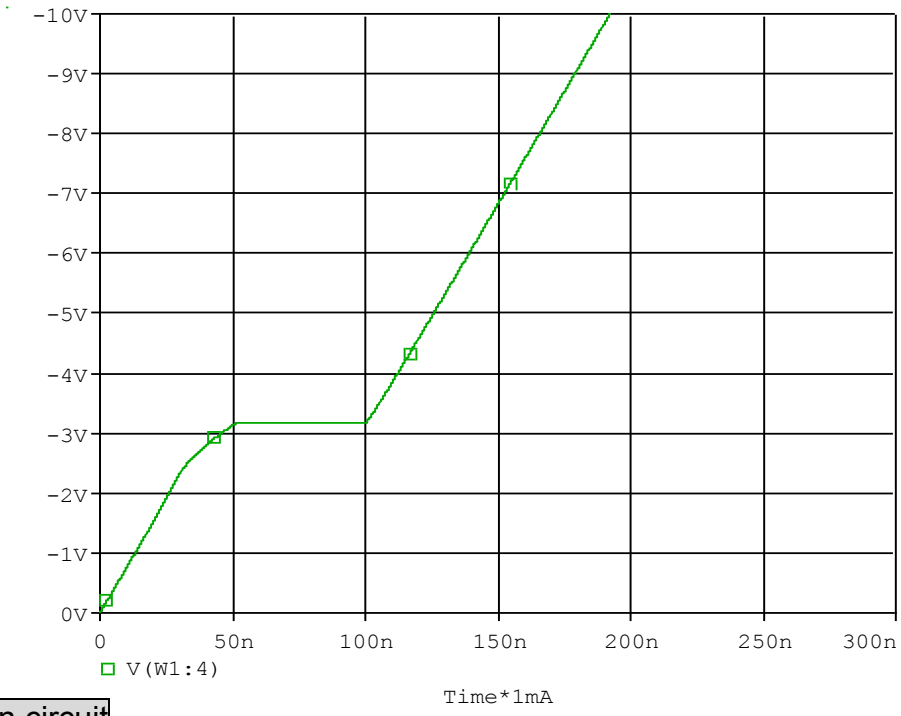


Simulation Result

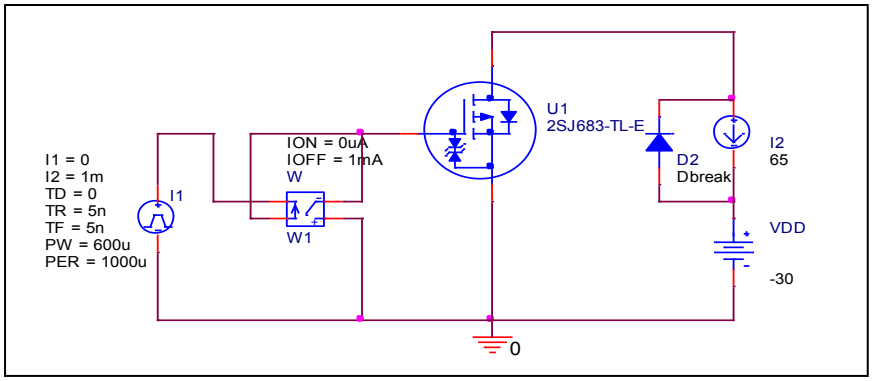
I_D= -33A, V_{GS}= -10V		Measurement	Simulation	Error (%)
R_{DS} (on)	mΩ	8.000	7.989	-0.14

Gate Charge Characteristic

Circuit Simulation result



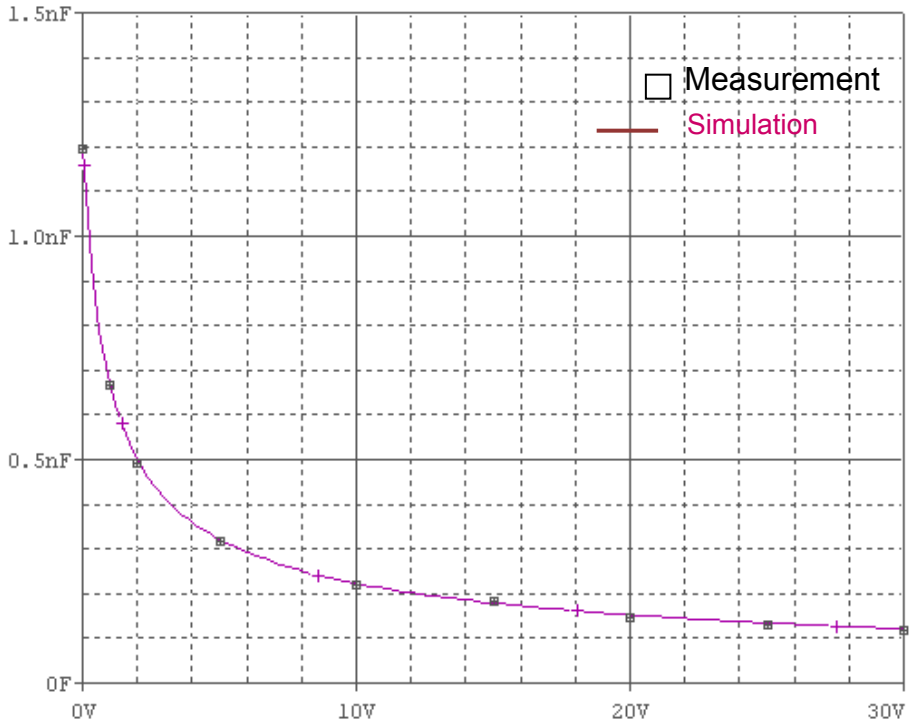
Evaluation circuit



Simulation Result

V_{DD}= -30V,I_D= -65A ,V_{GS}= -10V		Measurement	Simulation	Error (%)
Qgs	nC	50.000	50.257	0.51
Qgd	nC	50.000	50.437	0.87
Qg	nC	290.000	192.240	-33.71

Capacitance Characteristic

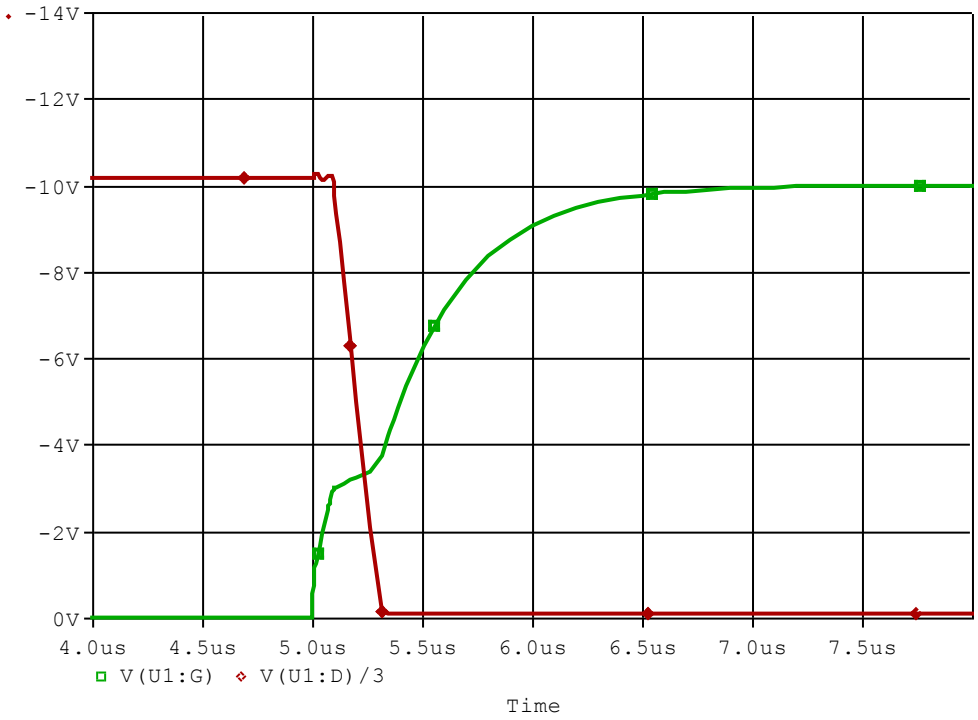


Simulation Result

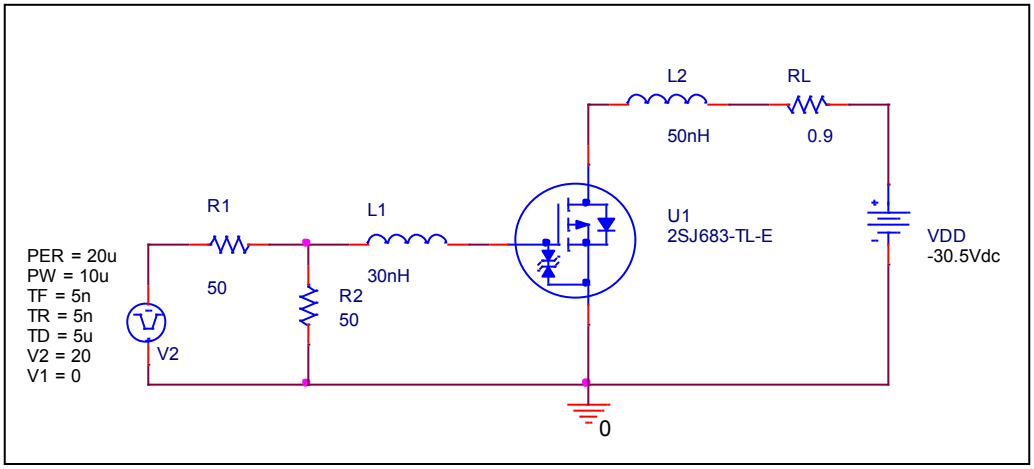
V_{SD}(V)	Cbd(pF)		Error(%)
	Measurement	Simulation	
0.0	1200.000	1198.000	-0.17
1.0	670.000	668.000	-0.30
2.0	498.000	502.000	0.80
5.0	320.000	323.000	0.94
10.0	225.000	223.000	-0.89
15.0	180.000	179.000	-0.56
20.0	152.000	153.000	0.66
25.0	135.000	134.000	-0.74
30.0	121.000	121.800	0.66

Switching Time Characteristic

Circuit Simulation result



Evaluation circuit

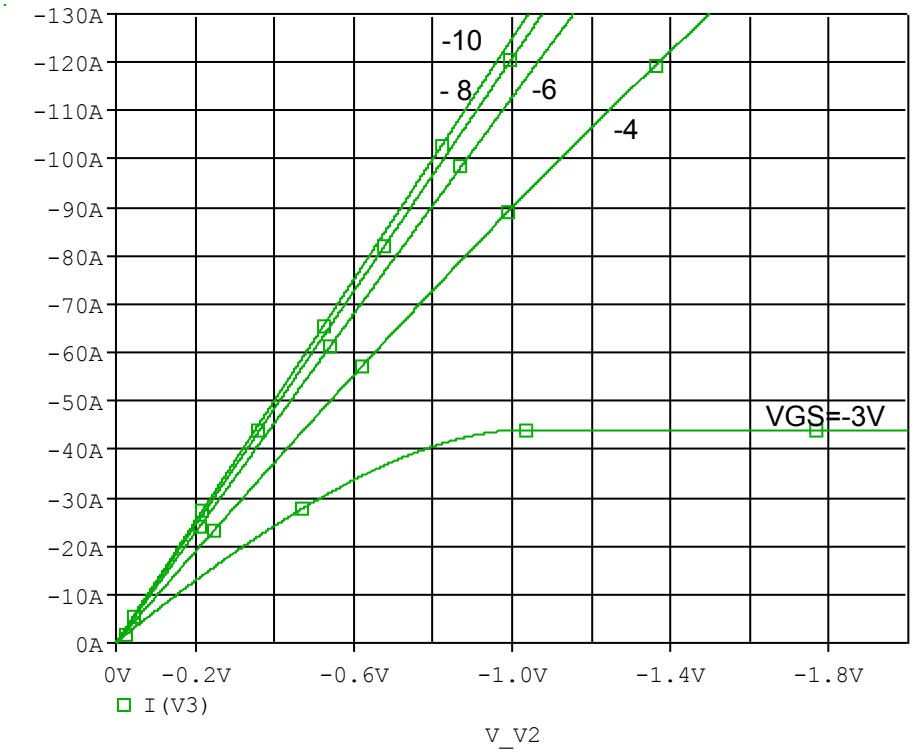


Simulation Result

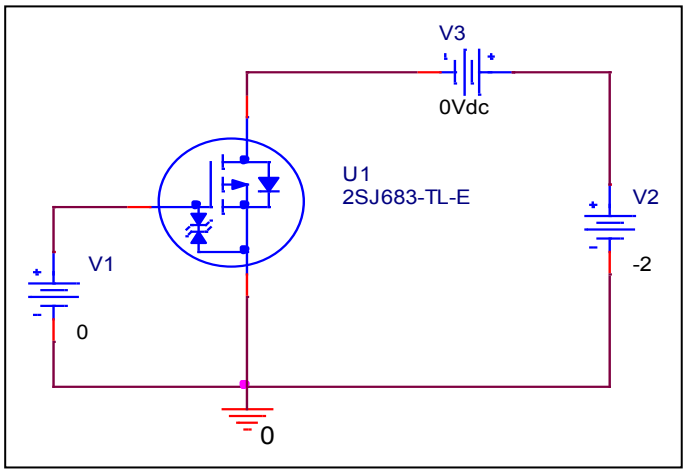
I_D= -33A, V_{DD}= -30V V_{GS}=0/-10V		Measurement	Simulation	Error(%)
td(on)	ns	110.000	110.012	0.01

Output Characteristic

Circuit Simulation result

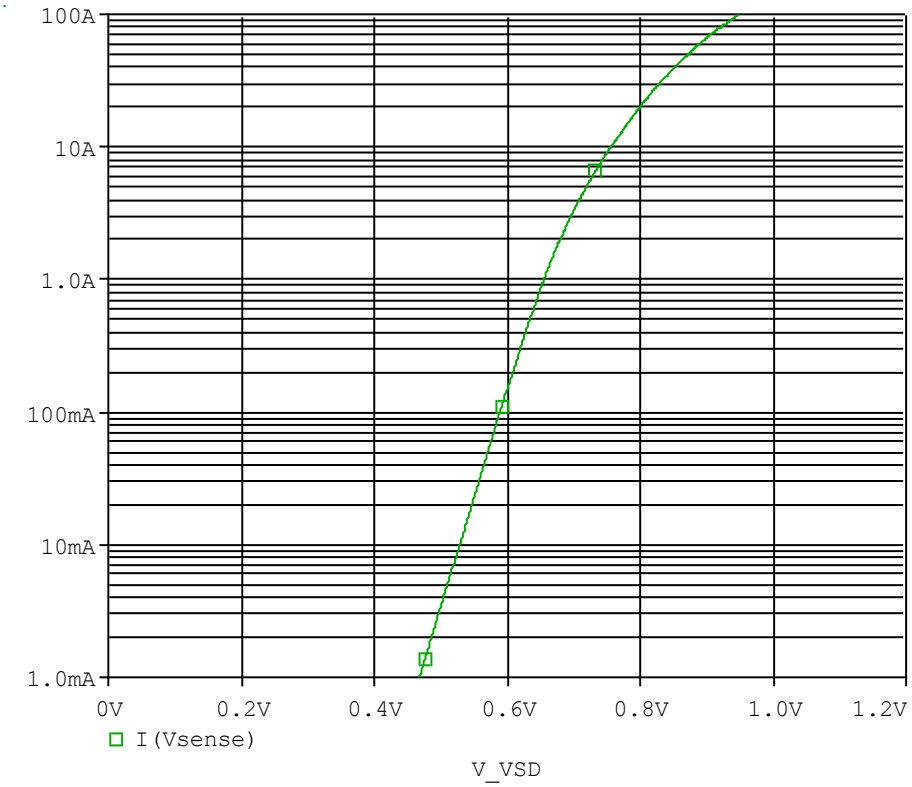


Evaluation circuit

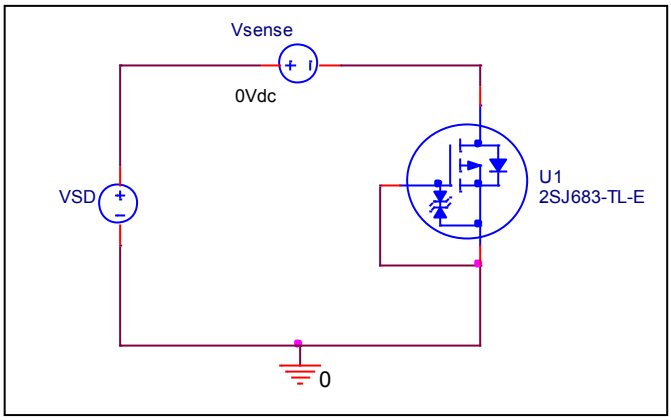


BODY DIODE SPICE MODEL
Forward Current Characteristic

Circuit Simulation Result

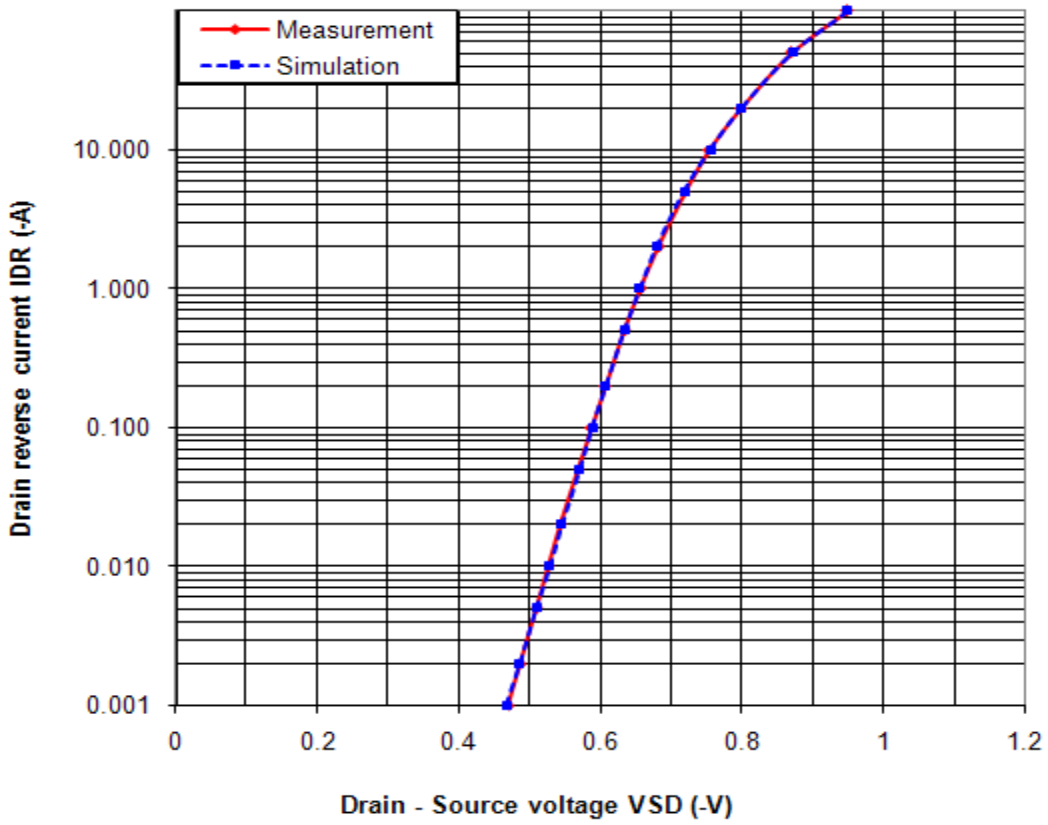


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

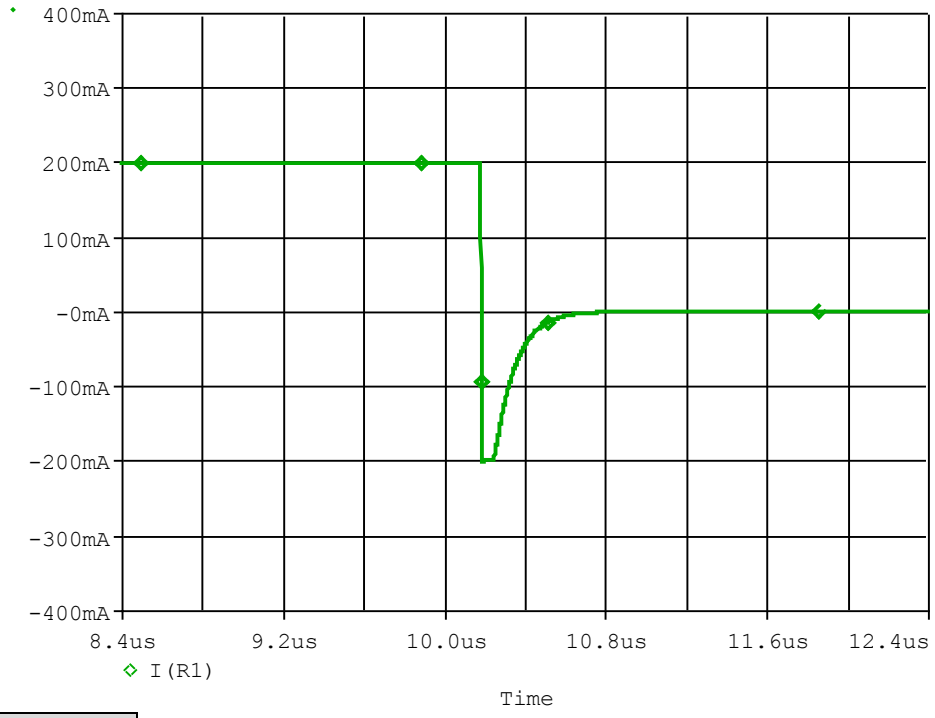


Simulation Result

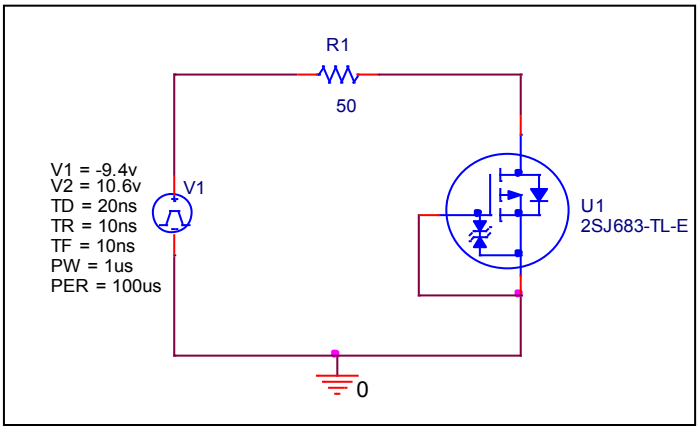
IDR(-A)	VSD (-V)		%Error
	Measurement	Simulation	
0.001	0.470	0.468	-0.43
0.001	0.527	0.528	0.19
0.100	0.588	0.589	0.17
1.000	0.657	0.655	-0.30
2.000	0.682	0.679	-0.38
5.000	0.720	0.719	-0.14
10.000	0.755	0.756	0.13
20.000	0.800	0.799	-0.13
50.000	0.870	0.872	0.23
100.000	0.950	0.949	-0.11

Reverse Recovery Characteristic

Circuit Simulation Result



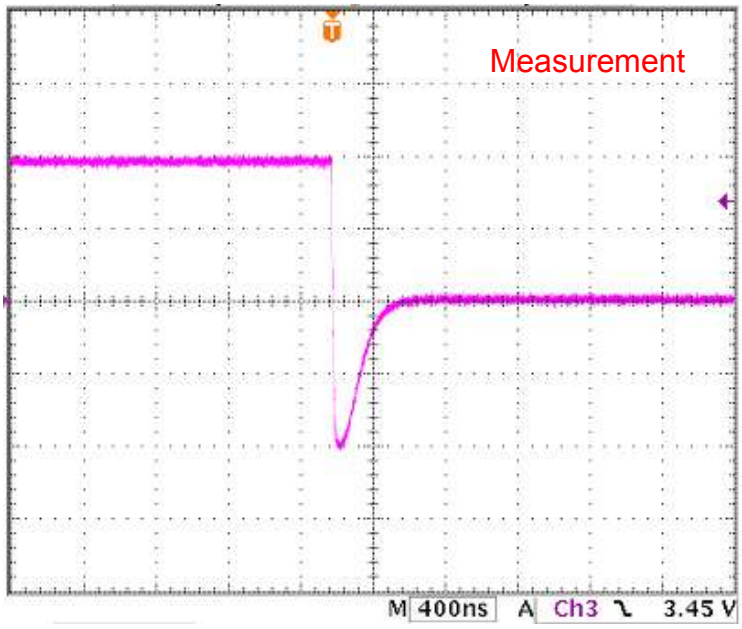
Evaluation Circuit



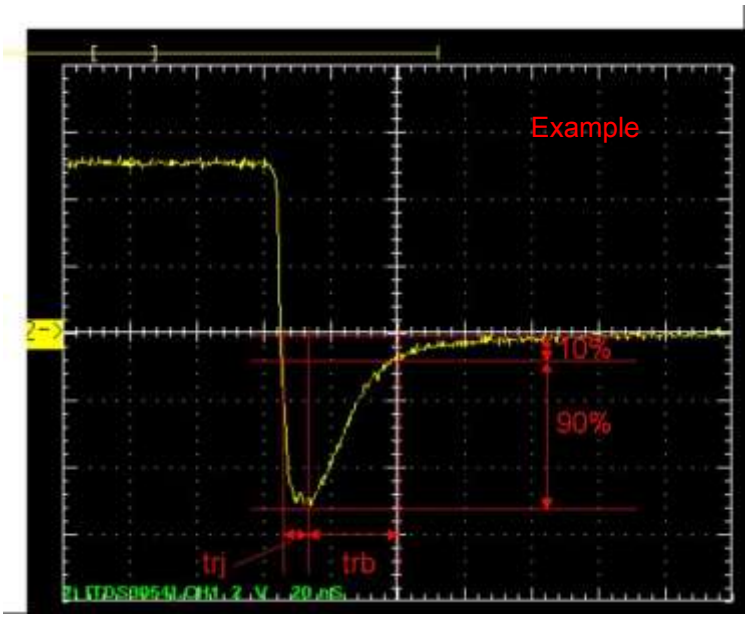
Compare Measurement vs. Simulation

		Measurement	Simulation	Error (%)
trj	ns	60.000	60.808	1.35

Reverse Recovery Characteristic Reference



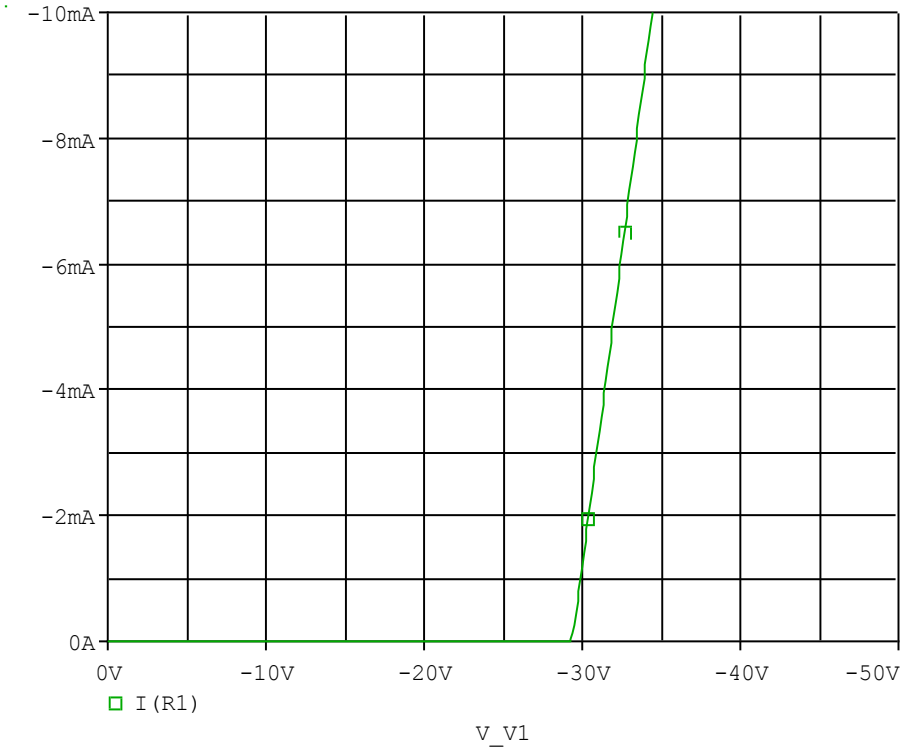
Trj= 60.00 (ns)
Trb=160.00 (ns)
Conditions:Ifwd=Irev=0.2(A),Rl=50



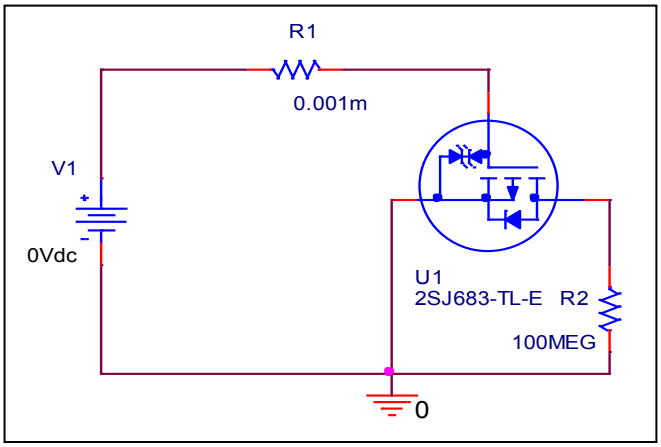
Relation between trj and trb

ESD PROTECTION DIODE SPICE MODEL
Zener Voltage Characteristic

Circuit Simulation Result



Evaluation Circuit



Zener Voltage Characteristic Reference